



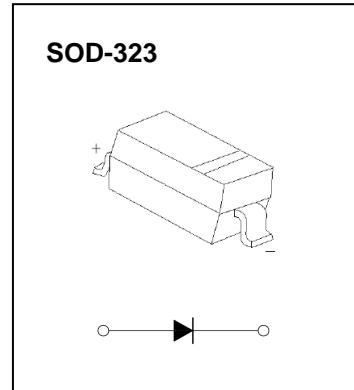
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOD-323 Plastic-Encapsulate Diodes

RB751V -40 Schottky Barrier Diode

FEATURES

- Low current rectifier schottky diode
- Low voltage, low inductance
- For power supply



MAKING: 5

Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
Peak reverse voltage	V _{RM}	40	V
DC reverse voltage	V _R	30	V
Mean rectifying current	I _O	0.03	A
Peak forward surge current	I _{FSM}	0.2	A
Power dissipation	P _D	200	mW
Thermal Resistance Junction to Ambient	R _{θJA}	500	°C/W
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55~+150	°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V _F			0.37	V	I _F =1mA
Reverse current	I _R			0.5	μA	V _R =30V
Capacitance between terminals	C _T		2		pF	V _R =1V, f=1MHZ

Typical Characteristics

RB751V-40

